

REMARKS

Reconsideration and further examination of the present application is respectfully requested.

Rejections Under 35 U.S.C. §§ 102(e), 103(a)

In paragraph 1 on pages 2-7 of the Final Office Action, claims 25-36, 38-55, and 57-60 are rejected under 35 U.S.C. § 102(e) as being anticipated by U.S. Patent No. 6,037,232 to Wieczorek et al. ("Wieczorek").

In paragraph 2 on pages 7-8 of the Final Office Action, claims 37 and 56 are rejected under 35 U.S.C. § 103(a) as being unpatentable over Wieczorek and U.S. Patent No. 5,880,500 to Iwata et al. ("Iwata").

Applicant respectfully traverses these rejections as follows.

Applicant respectfully submits neither Wieczorek nor Iwata, whether alone or in any combination with one another, taught or suggested a source/drain terminal comprising an implanted region in a substrate, a first silicide layer in the substrate, and a second silicide layer in the substrate, wherein the first silicide layer and the second silicide layer are both in the implanted region in the substrate, as claimed in independent claim 25.

Applicant also respectfully submits neither Wieczorek nor Iwata, whether alone or in any combination with one another, taught or suggested a source/drain terminal comprising a first implanted region in a substrate, a first silicide layer in the substrate, a second implanted region in the substrate, and a second silicide layer in the substrate, wherein the first silicide layer is in the

first implanted region in the substrate and the second silicide layer is in the second implanted region in the substrate, as claimed in independent claim 42.

Applicant respectfully submits only one of the two silicide layers 219B of Wieczorek is in a substrate. See, e.g., Fig. 2D.

Noting claims 26-41 and 43-60 depend from claim 25 or 42, Applicant respectfully submits these rejections have been overcome and should accordingly be withdrawn.

New Claims

New claims 61-62 depend from independent claim 25 or 42. Applicant therefore respectfully submits claims 61-62 are patentable over Wieczorek and Iwata.

VERSION WITH MARKINGS TO SHOW CHANGES MADE

25. (Amended Twice) A microelectronic structure comprising:

a substrate;

a gate electrode formed over the substrate; and

a source/drain terminal aligned with the gate electrode, the source/drain terminal comprising an implanted region in the substrate, a first silicide layer in the [implanted region] substrate, and a second silicide layer in the [implanted region] substrate,

wherein the first silicide layer and the second silicide layer are both in the implanted region in the substrate.

42. (Amended Twice) A microelectronic structure comprising:

a substrate;

a gate electrode formed over the substrate; and

a source/drain terminal aligned with the gate electrode, the source/drain terminal comprising a first implanted region in the substrate, a first silicide layer in the [first implanted region] substrate, a second implanted region in the substrate, and a second silicide layer in the [second implanted region] substrate,

wherein the first silicide layer is in the first implanted region in the substrate and the second silicide layer is in the second implanted region in the substrate.

Claims 61-62 have been added.

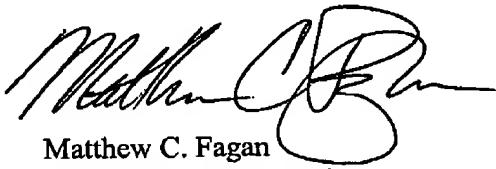
In view of the foregoing, it is respectfully submitted the present application is in condition for allowance, for which early action is earnestly solicited.

The Examiner is invited to telephone the undersigned to help expedite any further prosecution of the present application.

The Director of the U.S. Patent and Trademark Office is hereby authorized to credit any overpayment or to charge any fees or fee deficiencies under 37 C.F.R. §§ 1.16 and 1.17 in connection with this communication to our Deposit Account No. 02-2666.

Respectfully submitted,

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